

ABSTRACT OF THE DISCLOSURE

The substrate processing apparatus is provided with a gas-liquid mixing nozzle for generating a gas-liquid mixture by mixing a liquid and a pressurized gas, to
5 discharge the gas-liquid mixture to a substrate at high speeds. The mixture process is conducted in an open space out of the nozzle, and change in the supply pressure of the gas does not affect the supply of the liquid. The reaction products which having been generated on the substrate in etching process is removed at high speeds with the flow of the gas-liquid mixture, whereby the quality of the process is improved.